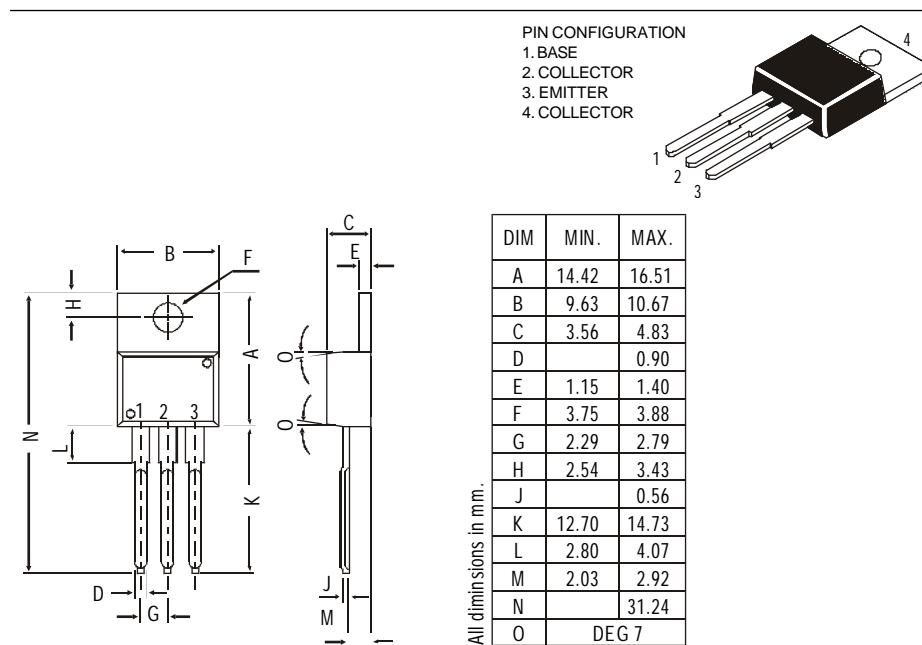




TO-220 Plastic Package

BDX53, BDX53A, BDX53B, BDX53C  
BDX54, BDX54A, BDX54B, BDX54C

*BDX53, 53A, 53B, 53C      NPN PLASTIC POWER TRANSISTORS  
BDX54, 54A, 54B, 54C      PNP PLASTIC POWER TRANSISTORS  
Power Darlingtons for Linear and Switching Applications*



**ABSOLUTE MAXIMUM RATINGS**

	53	53A	53B	53C		
	54	54A	54B	54C		
Collector-base voltage (open emitter)	$V_{CBO}$	max. 45	60	80	100	V
Collector-emitter voltage (open base)	$V_{CEO}$	max. 45	60	80	100	V
Collector current	$I_C$	max.		8.0		A
Total power dissipation up to $T_C = 25^\circ C$	$P_{tot}$	max.		60		W
Junction temperature	$T_j$	max.		150		$^\circ C$
Collector-emitter saturation voltage $I_C = 3 A; I_B = 12 mA$	$V_{CEsat}$	max.		2.0		V
D.C. current gain $I_C = 3 A; V_{CE} = 3 V$	$h_{FE}$	min.		750		

**RATINGS** (at  $T_A=25^\circ C$  unless otherwise specified)

Limiting values	53	53A	53B	53C		
	54	54A	54B	54C		
Collector-base voltage (open emitter)	$V_{CBO}$	max. 45	60	80	100	V
Collector-emitter voltage (open base)	$V_{CEO}$	max. 45	60	80	100	V
Emitter-base voltage (open collector)	$V_{EBO}$	max.		5.0		V

**BDX53, BDX53A, BDX53B, BDX53C**  
**BDX54, BDX54A, BDX54B, BDX54C**

<i>Collector current</i>	$I_C$	max.	8.0	A
<i>Collector current (Peak value)</i>	$I_{CM}$	max.	12	A
<i>Base current</i>	$I_B$	max.	0.2	A
<i>Total power dissipation upto <math>T_C=25^\circ C</math></i>	$P_{tot}$	max.	60	W
<i>Derate above <math>25^\circ C</math></i>		max.	0.48	$W^\circ C$
<i>Junction temperature</i>	$T_j$	max.	150	$^\circ C$
<i>Storage temperature</i>	$T_{stg}$		-65 to +150	$^\circ C$
<b>THERMAL RESISTANCE</b>				
<i>From junction to case</i>	$R_{thj-c}$		2.08	$^\circ CW$
<i>From junction to ambient</i>	$R_{thj-a}$		7.0	$^\circ CW$

**CHARACTERISTICS**

$T_{amb} = 25^\circ C$  unless otherwise specified

		53	53A	53B	53C	
		54	54A	54B	54C	
<i>Collector cutoff current</i>						
$I_B = 0; V_{CB} = 45 V$	$I_{CBO}$	max.	0.2	-	-	- mA
$I_B = 0; V_{CB} = 60 V$	$I_{CBO}$	max.	-	0.2	-	- mA
$I_B = 0; V_{CB} = 80 V$	$I_{CBO}$	max.	-	-	0.2	- mA
$I_B = 0; V_{CB} = 100 V$	$I_{CBO}$	max.	-	-	-	0.2 mA
$I_B = 0; V_{CE} = 22 V$	$I_{CEO}$	max.	0.5	-	-	- mA
$I_B = 0; V_{CE} = 30 V$	$I_{CEO}$	max.	-	0.5	-	- mA
$I_B = 0; V_{CE} = 40 V$	$I_{CEO}$	max.	-	-	0.5	- mA
$I_B = 0; V_{CE} = 50 V$	$I_{CEO}$	max.	-	-	-	0.5 mA
<i>Emitter cut-off current</i>						
$I_C = 0; V_{EB} = 5 V$	$I_{EBO}$	max.		2.0		mA
<i>Breakdown voltages</i>						
$I_C = 100 mA; I_B = 0$	$V_{CEO(sus)}^*$	min.	45	60	80	100 V
$I_C = 1 mA; I_E = 0$	$V_{CBO}$	min.	45	60	80	100 V
$I_E = 1 mA; I_C = 0$	$V_{EBO}$	min.		5.0		V
<i>Saturation voltages</i>						
$I_C = 3 A; I_B = 12 mA$	$V_{CESat}^*$	max.		2.0		V
	$V_{BEsat}^*$	max.		2.5		V
<i>D.C. current gain</i>						
$I_C = 3 A; V_{CE} = 3 V$	$h_{FE}^*$	min.		750		
<i>Small signal current gain</i>						
$I_C = 3 A; V_{CE} = 4 V; f = 1.0 \text{ MHz}$	$ h_{fe} $	min.		4.0		
<i>Output capacitance <math>f = 1.0 \text{ MHz}</math></i>						
$I_E = 0; V_{CB} = 10 V$	$C_o$	max.		300		pF
	$C_o$	max.		200		pF
<i>Parallel-diode forward voltage</i>						
$I_F = 3 A$	$V_F$	max.		2.5		V
$I_F = 8 A$	$V_F$	typ.		2.5		V

\* Pulse test: pulse width  $\leq 300 \mu s$ ; duty cycle  $\leq 2\%$